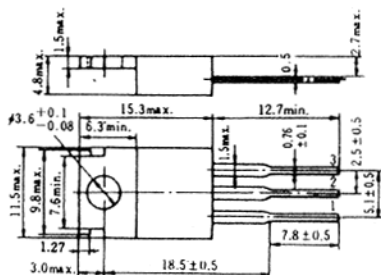


2SB860

SILICON PNP TRIPLE DIFFUSED
 LOW FREQUENCY POWER AMPLIFIER
 TV VERTICAL DEFLECTION OUTPUT
 COMPLEMENTARY PAIR WITH 2SD1137



1. Base
 2. Collector
 (Flange)
 3. Emitter
 (Dimensions in mm)

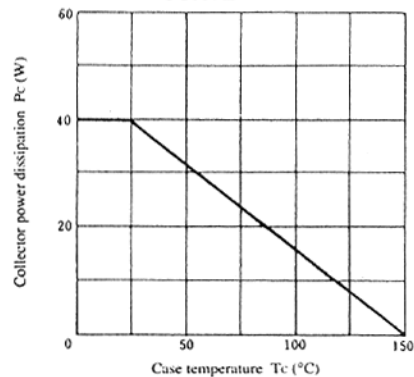
(JEDEC TO-220AB)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB860	Unit
Collector to base voltage	VCBO	-100	V
Collector to emitter voltage	VCEO	-100	V
Emitter to base voltage	VEBO	-4	V
Collector current	IC	-4	A
Collector peak current	iC(peak)	-5	A
Collector power dissipation	PC	1.8	W
	PC*	40	W
Junction temperature	Tj	150	°C
Storage temperature	Tsig	-45 to +150	°C

* Value at Tc = 25°C

MAXIMUM COLLECTOR DISSIPATION CURVE

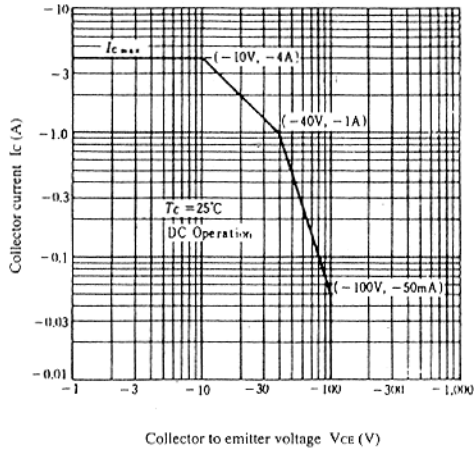


■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

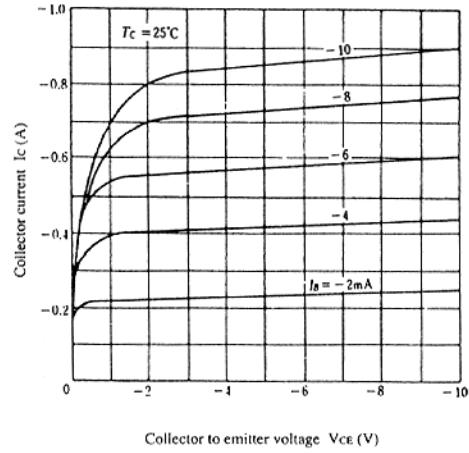
Item	Symbol	Test Condition	min.	typ.	max.	Unit	
Collector to emitter breakdown voltage	V(BR)CEO	IC = -10mA, RBE = ∞	-100	—	—	V	
Emitter to base breakdown voltage	V(BR)EBO	IE = -1mA, IC = 0	-4	—	—	V	
Collector cutoff current	ICEO	VCE = -80V, RBE = ∞	—	—	-100	μA	
Emitter cutoff current	IEBO	VEB = -3.5V, IC = 0	—	—	-50	μA	
Collector to emitter saturation voltage	VCE(sat)	IC = -1A, IB = -0.1A*	—	—	-1.0	V	
DC current transfer ratio	hFE	VCE = -4V	IC = -0.5A*	50	—	250	
			IC = -50mA	25	—	350	

* Pulse Test

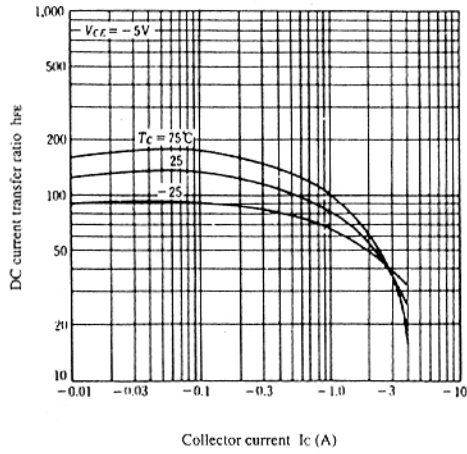
AREA OF SAFE OPERATION



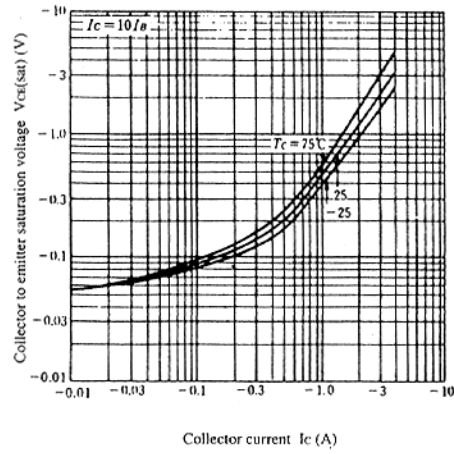
TYPICAL OUTPUT CHARACTERISTICS



DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



COLLECTOR TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT



BASE TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT

